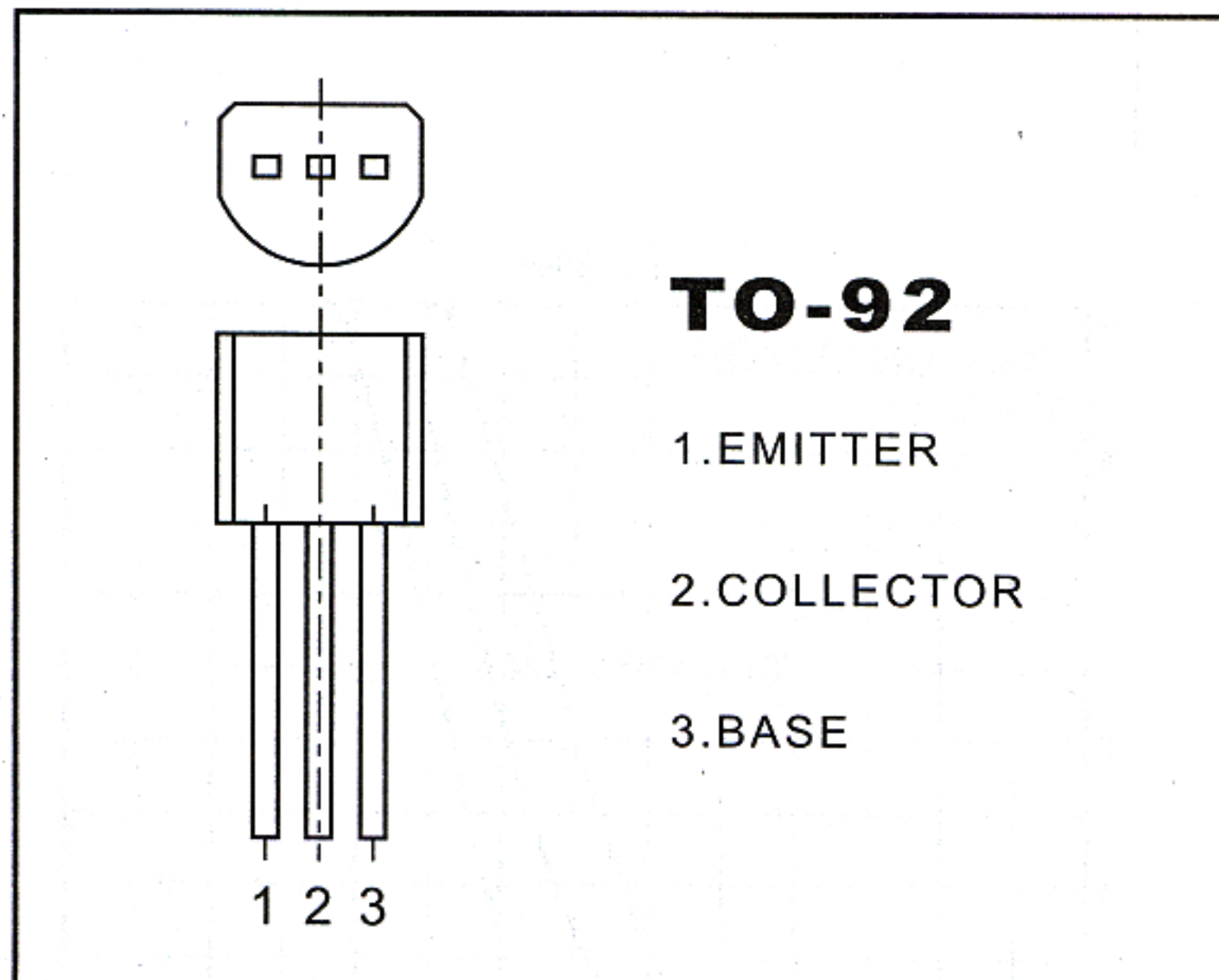


2SC3279 TRANSISTOR(NPN)



FEATURES

Power dissipation

P_{CM} : 0.75W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 2 A

Collector-base voltage

$V_{(BR)CBO}$: 30 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	30		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	10		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB}=30V, I_E=0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=6V, I_C=0$		0.1	μA
DC current gain	h_{FE}	$V_{CE}=1V, I_C=0.5mA$	140	600	
Collector-emitter saturation voltage	V_{CEsat}	$I_C=2A, I_B=50mA$		0.5	V
Base-emitter voltage	V_{BE}	$V_{CE}=1V, I_C=2A$		1.5	V
Transition frequency	f_t	$V_{CE}=1V, I_C=0.5mA$ $f=30MHz$	100		MHz

CLASSIFICATION OF h_{FE}

Rank	L	M	N	P
Range	140-240	200-330	300-450	420-600

